Process flow title			Revision
AZ nLOF 2020 on SiO_2			**1.1**
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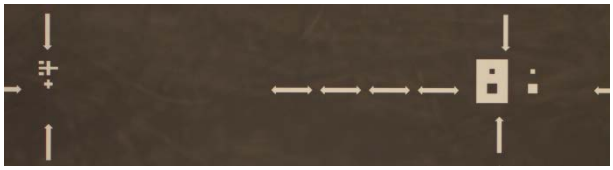
Objective

Batch name: Litho TPT alignment

This process flows is a guideline on how to prime, spin coat, expose, develop, and inspect 2 µm AZ MiR 701 on oxidized Si substrates using Spin Coater: Gamma UV, Aligner: MA6-2 / KS Aligner, and Developer: TMAH UV-lithography.

Step	Header	Equipment		Comments
1	**Spin coating of AZ nLOF 2020 with HMDS priming**			
1.1	Coat wafers	Spin Coater: Gamma UV	**Resist:** AZ nLOF 2020 (Resist 2) **HMDS priming:** 15 s @ 120°C (contact angle ~70°) **Spin:** 30 s @ 3300 rpm (~2 µm) **Softbake:** 60 s @ 110 °C **Sequence:** (2421) DCH 100mm nLOF 2020 2um HMDS	Substrates: Processed Si with GreenBelt N+ and GreenBelt CONTACTS layers. The surface is etched SiO_2 (~90 nm).
2	**UV Exposure**			
2.1	Exposure	Aligner: MA6 – 2 or KS Aligner	**Mask:** GreenBelt METAL **Exposure mode:** Hard contact HC wait time: 10 s Alignment gap: 20 µm **Exposure dose:** 112 mJ/cm^2 for MA6 – 2 98 mJ/cm^2 for KS **Alignment marks:** X=±43mm; Y=0mm mask:  substrate: 	Exposure time: 8.6s @ 13mW/cm^2 for MA6-2 14s @ 7mW/cm^2 for KS
3	**Development with PEB**			
3.1	Develop	Developer: TMAH UV-lithography	**Post Exposure Bake:** 60 s @ 110°C **Development in AZ 726 MIF:** single puddle, 60 s **Sequence:** (3001) DCH 100mm PEB60s@110C+SP60s	PEB and development is done sequentially
4	**Inspection**			
4.1	Inspection	Optical microscope	**Inspect:** Verniers (X and Y) for alignment accuracy (possible also monitor structures for resolution)